

Low Gain Avalanche Detectors for the ATLAS High Granularity Timing Detector: laboratory and test beam campaigns

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On behalf of the ATLAS HGTD Group

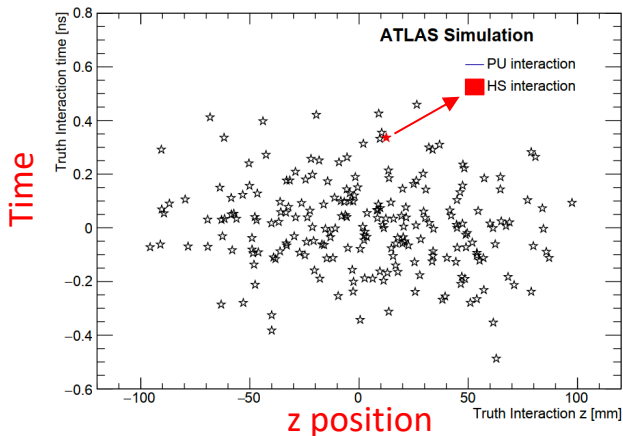
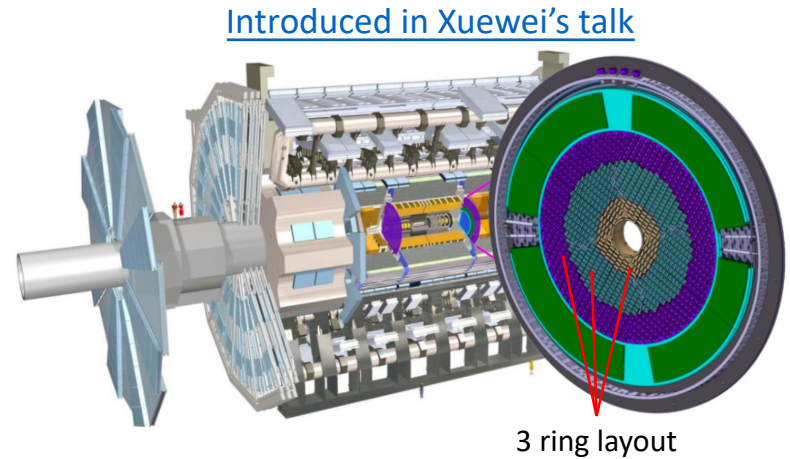
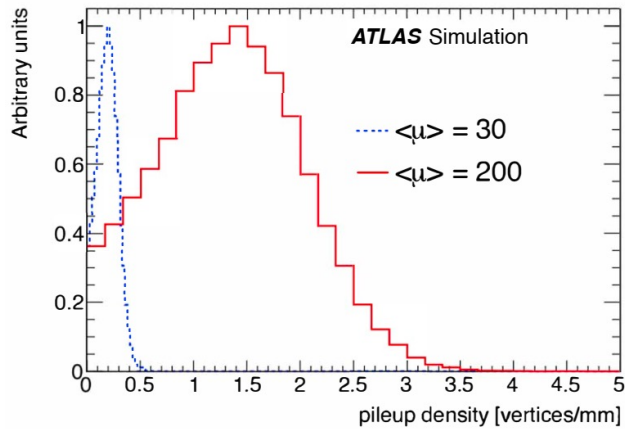
Sep 5th, 2023

Outline

- ATLAS HGTD upgrade and LGAD technology
- LGAD performance in Laboratory
 - Evolution of radiation hardness
 - Collected charge and time resolution with ^{90}Sr source
- LGAD performance in DESY and CERN test beam
 - LGAD Single Event Burnout
 - Collected charge, time resolution and hit efficiency
- Summary and outlook

ATLAS High Granularity Timing Detector (HGTD)

- High-Luminosity phase of LHC (HL-LHC): It's hard to associate track to primary vertex in **high pileup environment**, especially in the forward region ($2.4 < |\eta| < 4.0$)
- High-Granularity Timing Detector (HGTD): to measure **high-precision time of charged particles** in the forward region, complementing the Inner Tracker (ITk)

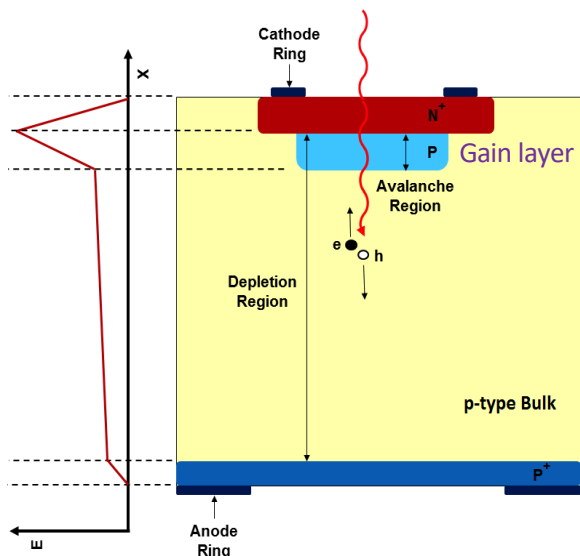


HGTD requirements:

- Withstand intense radiation environment
 - Maximum fluence: $2.5E15 \text{ n}_{eq}/\text{cm}^2$
 - Total Ionising Dose (TID): 2 MGy
- Collected charge per hit $> 4 \text{ fC}$
- time resolution: 35 ps (start), 70 ps (end) per hit / 30 ps (start), 50 ps (end) per track
- Hit efficiency of 97% (95%) at the start (end)

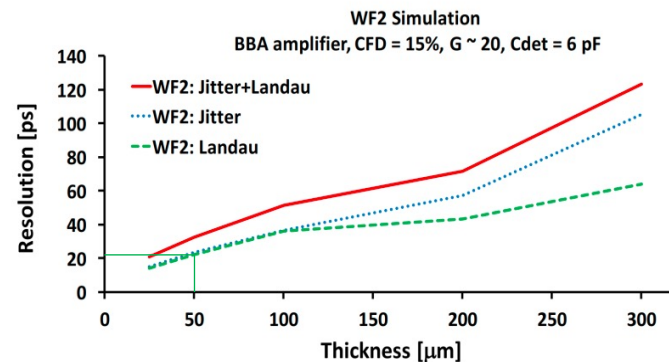
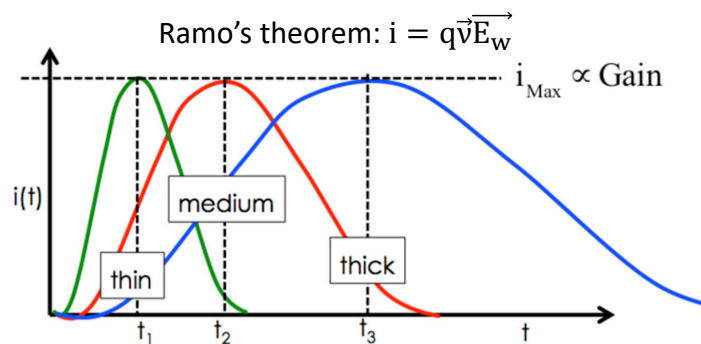
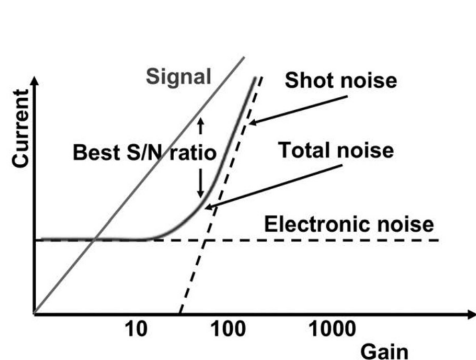
Low Gain Avalanche Detector (LGAD)

- N⁺-P-P⁻-P⁺ structure, moderate gain (10 ~ 20), ps time resolution (~ 30 ps) and mm position resolution (Granularity: 1.3 × 1.3 mm²)



$$\sigma_t^2 = \sigma_{\text{Jitter}}^2 + \sigma_{\text{Time Walk}}^2 + \sigma_{\text{Landau}}^2 + \sigma_{\text{Distortion}}^2 + \sigma_{\text{TDC}}^2$$

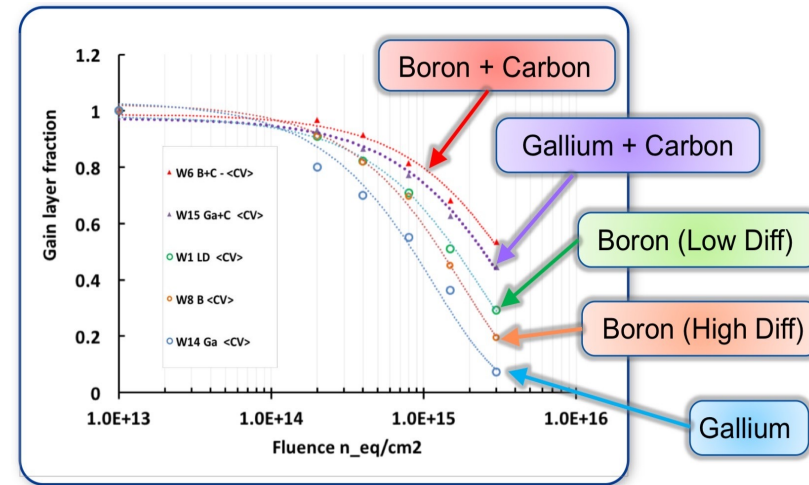
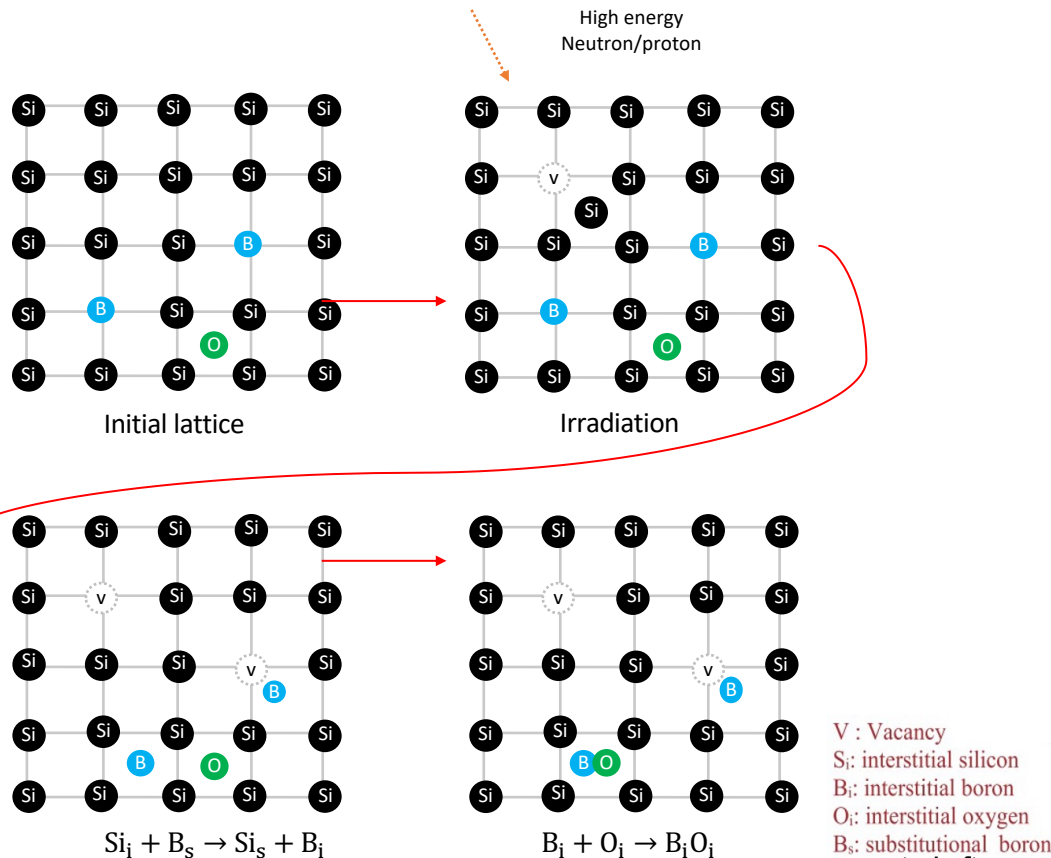
- $\sigma_{\text{Jitter}} \sim \frac{t_{\text{rise}}}{S/N}$, where t_{rise} is rise time and S/N is signal to noise ratio
- $\sigma_{\text{Time Walk}} \sim \left[\frac{V_{\text{th}}}{S/t_{\text{rise}}} \right]_{\text{RMS}}$, where V_{th} is threshold
- σ_{Landau} : caused by non-uniform energy deposition
- $\sigma_{\text{Distortion}}$: caused by non-saturated velocity v and non-uniform weighting field E_w
- $\sigma_{\text{Time-to-Digital Convert (TDC)}} \sim 25/\sqrt{12}$ (7.2) ps, can be neglected



Moderate gain (larger S/N), thin detector (50 μm, faster rise time) and finite segment (Granularity: 1.3 × 1.3 mm², uniform weight field) → fast timing

Low Gain Avalanche Detector (LGAD) R&D

- The **reduction of effective doping** in the gain layer is caused by the “**acceptor removal**” process -> LGADs’ gain reduces [M. Ferrero et al, NIMA, 2019](#) [G. Kramberger et al, 2015 JINST 10 P07006](#)
- Explored use of **different designs, doping materials and C-enriched substrates** -> Boron + Carbon shows largest gain after irradiation ($C_i + O_i \rightarrow C_iO_i$ competes with $B_i + O_i \rightarrow B_iO_i$)

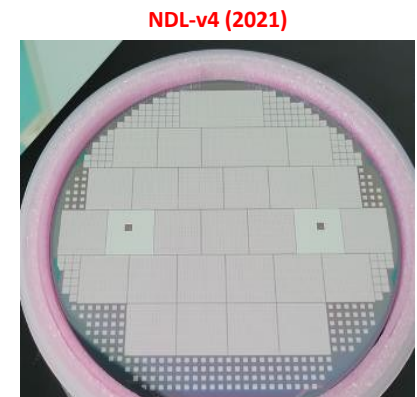
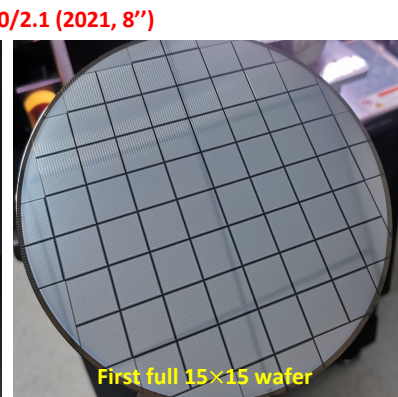
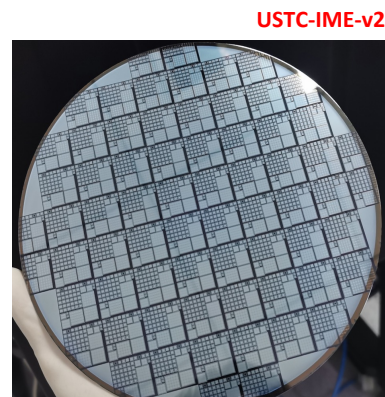
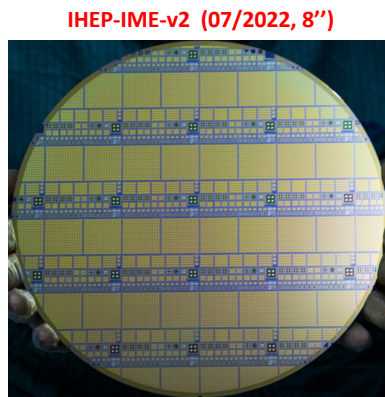
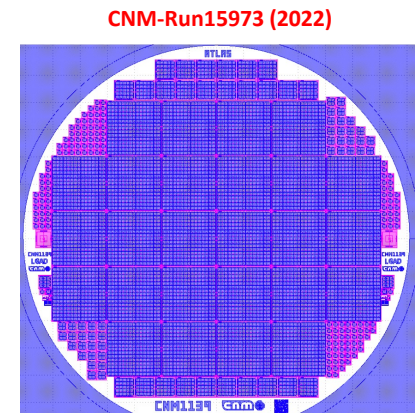
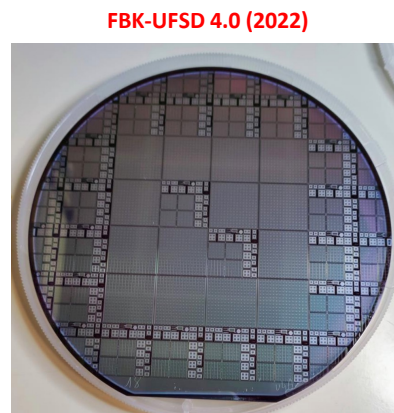
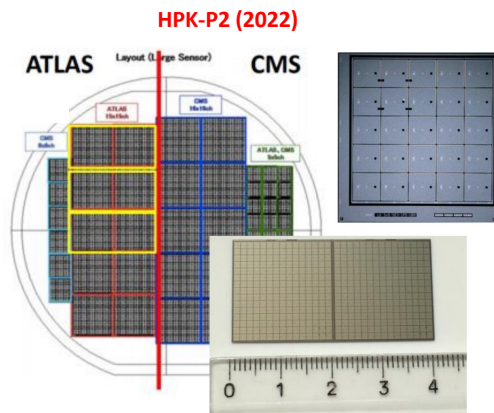


[G.Paternoster, TREDI 2019](#)

Acceptor (B_s) removal in the gain layer after irradiation

Latest prototypes produced by different vendors

- LGADs has been widely studied by many producers in last few years, including:
 - CNM (Spain), FBK (Italy), HPK (Japan), IHEP-IME (China), USTC-IME (China), IHEP-NDL (China) ...
- For each vender, the prototypes includes **small-array** sensors (1×1 , 2×2 ...) and **large-array** sensors (5×5 and full-size (15×15) sensor for ATLAS)

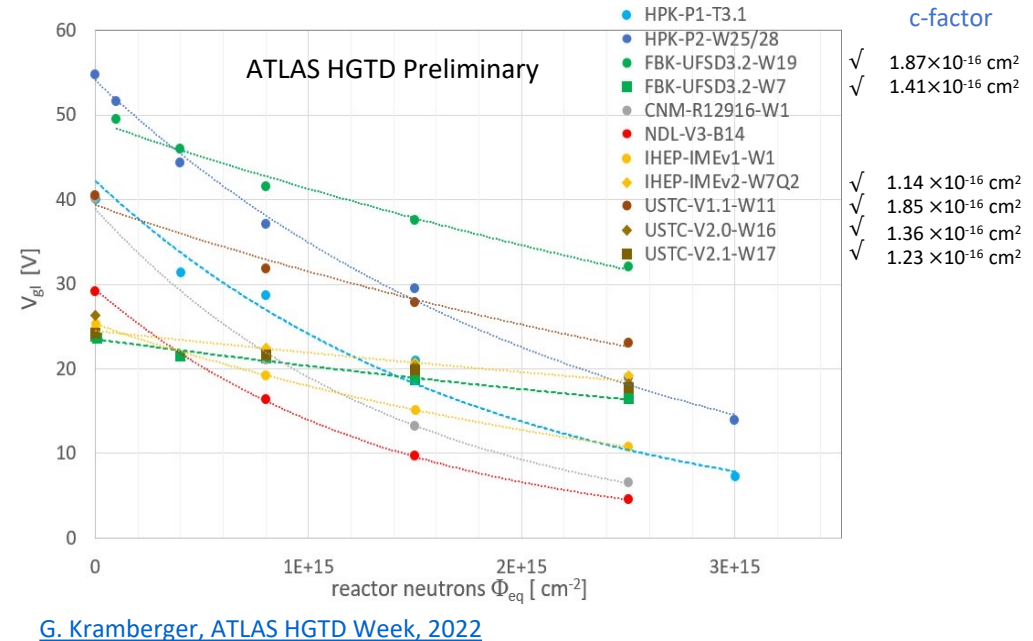
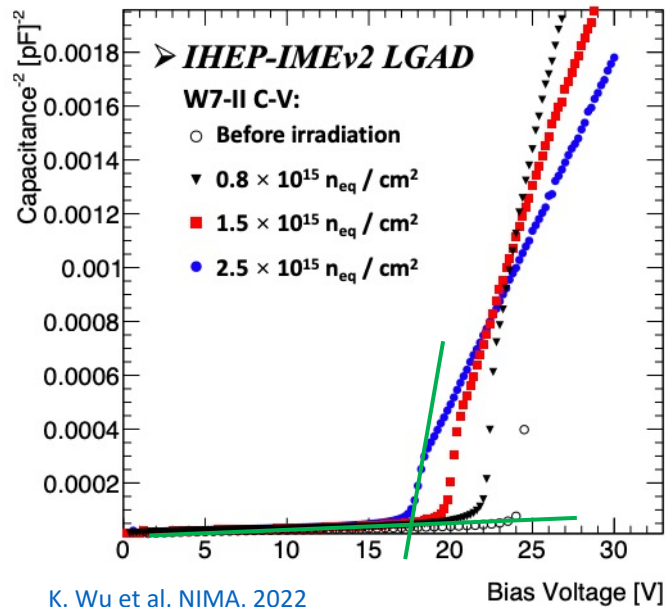


Evolution of radiation hardness

- The key parameter: **acceptor removal coefficient (c-factor)** (the lower the better)

$$V_{gl} = V_{gl0} \times \exp(-c \times \Phi_{eq})$$

- Optimization directions: adjust carbon enrichment dose and diffusion techniques



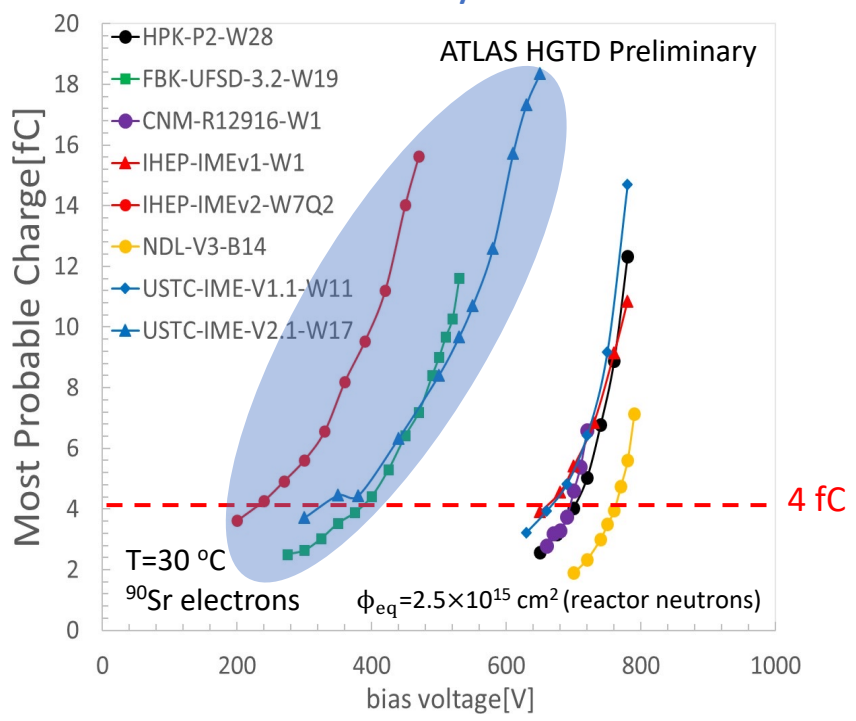
V_{gl} (V_{gl0}), depletion voltage of gain layer (before irradiation), is the voltage value where the two green straight lines intersect

FBK, IHEP-IME, USTC-IME have shown so far to master the process!

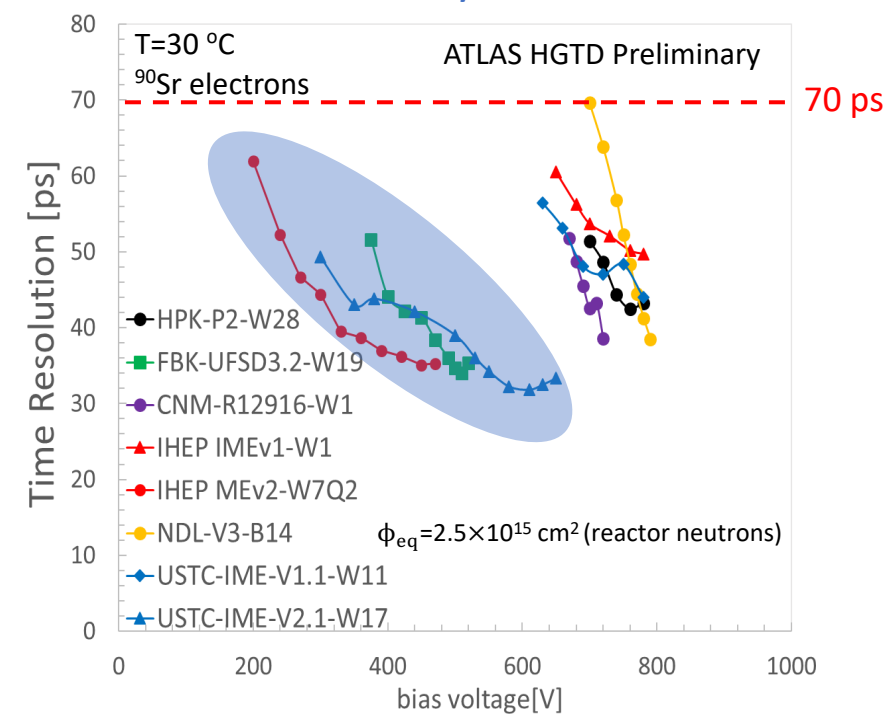
Collected charge and time resolution with ^{90}Sr source

- Sensors were exposed to fluence up to $2.5 \times 10^{15} \text{ n}_{\text{eq}}/\text{cm}^2$ at the TRIGA reactor in Ljubljana, Slovenia with fast neutrons
- After irradiation LGADs' performance degrades due to loss of gain -> increase of bias voltage to recover
- **Carbon-enriched** LGAD (blue region) allows the sensors to be operated at lower voltages

Laboratory results

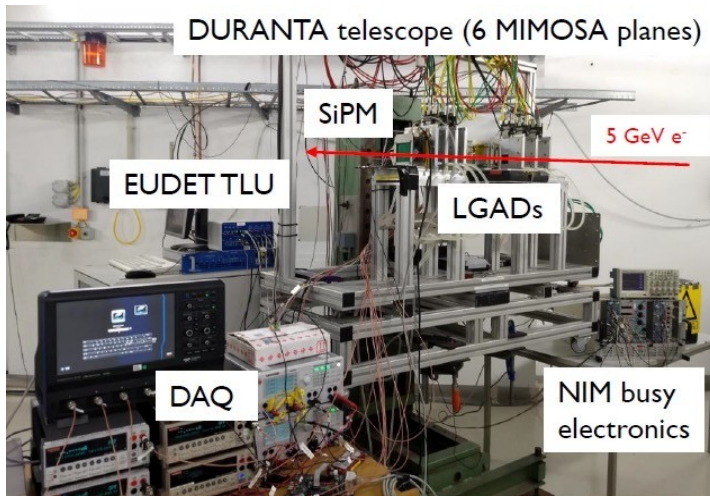


Laboratory results



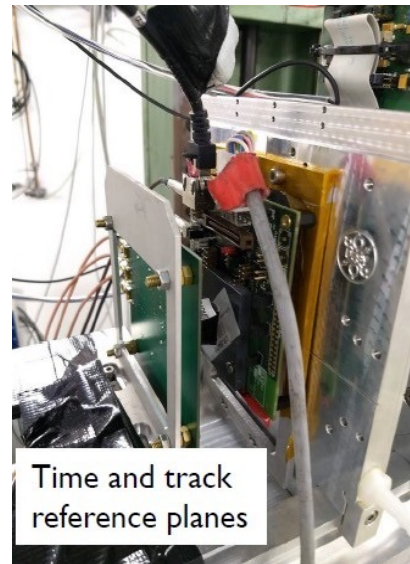
Beam test campaigns

- The collaboration has carried out numerous test beam campaigns and the results are documented in this list of papers: 2018 JINST 13 P06017, 2022 JINST 17 P09026 (2018-2019 data), **2023 JINST 18 P07030 (2021 data), 2023 JINST 18 P05005 (2021 - 2022 data)**
 - Determine safe bias voltages to avoid “Single Event Burnout” (SEB)
 - Qualify carbon-enriched LGADs performance (collected charge, time resolution, and hit efficiency)
 - DESY T22 beamline (5 GeV e^- beam) and CERN North Area SPS H6A beamline (120 GeV pion beam)
 - Use of beam telescope for tracking

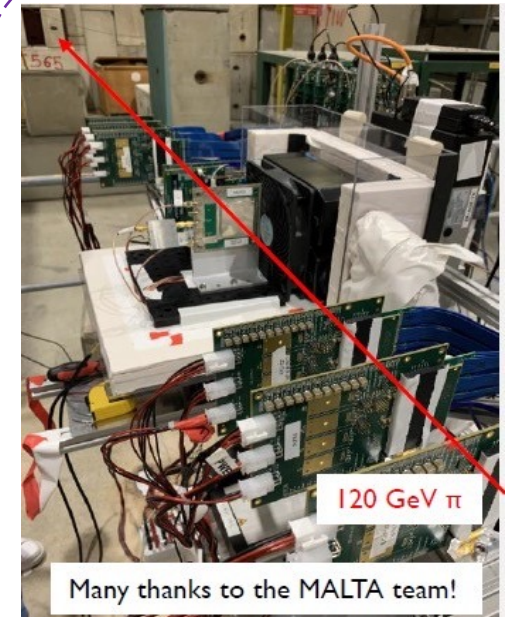


Set-up at DESY

Kuo Ma



PSD13, Oxford, 2023

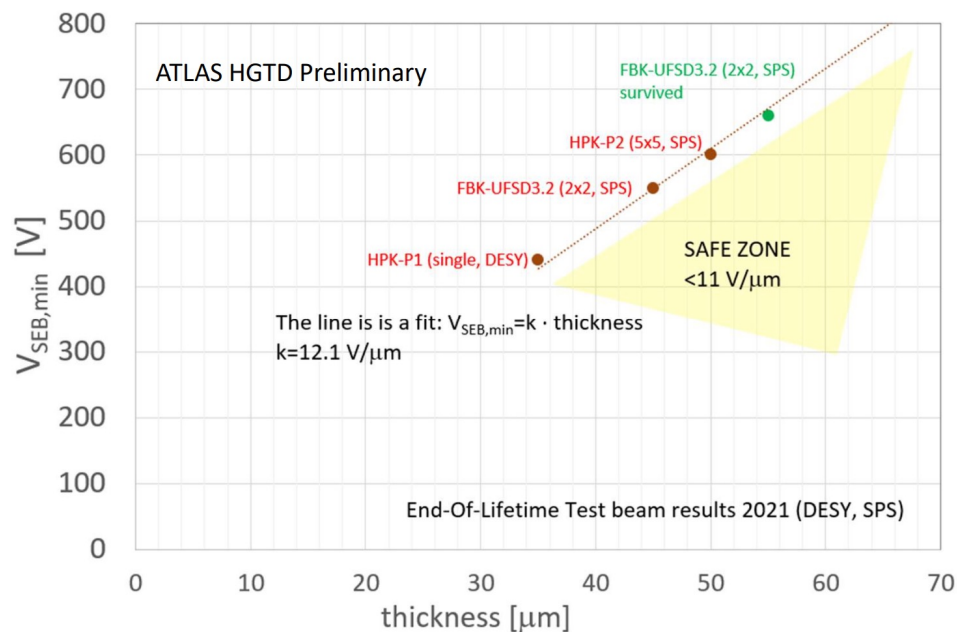
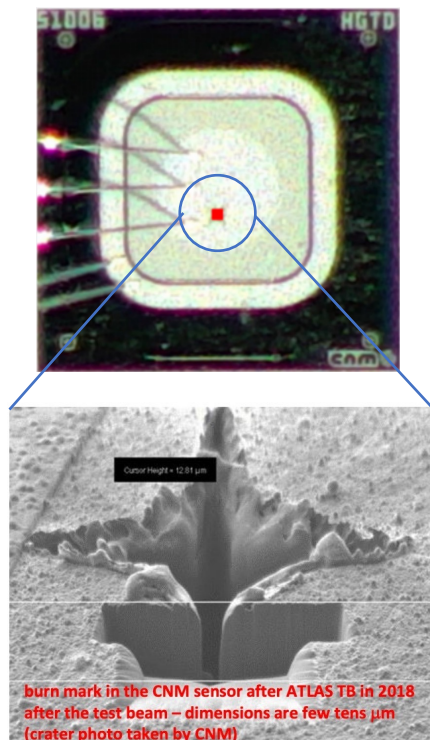


Set-up at CERN

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LGAD Single Event Burnout (SEB)

- Single Event Burnout (SEB) has been observed in several test beam campaigns
 - Irreversible breakdown while operating at high voltage (~ 100 V lower than voltage at laboratory)
 - Observed by CMS/ATLAS/RD50 teams [More details in Xuewei's talk](#)
- A safe zone has been defined
 - **Safe zone:** electric field < 11 V/ μm ($50 \mu\text{m} \rightarrow$ Max bias voltage is 550 V)



C-enriched LGAD prototypes for HGTD

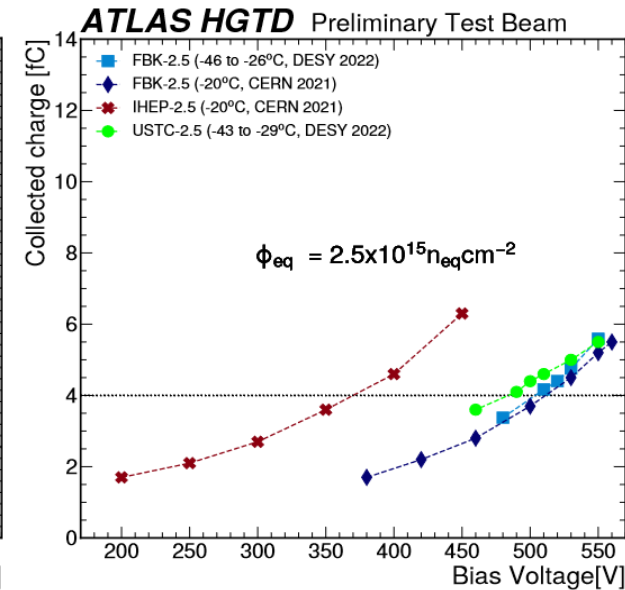
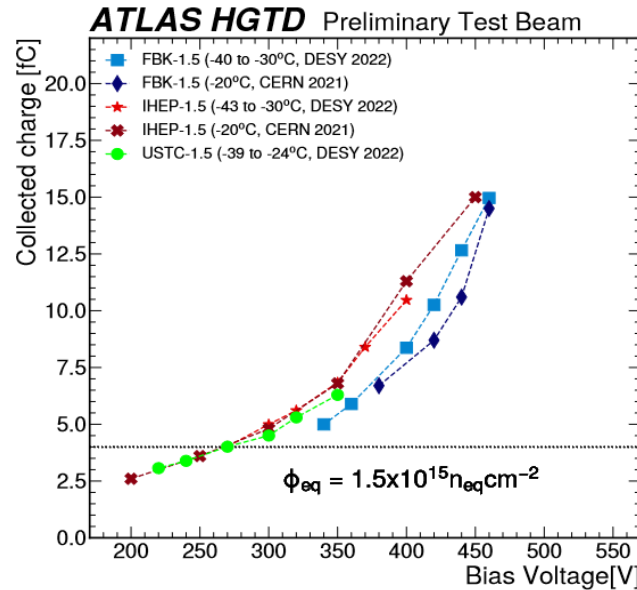
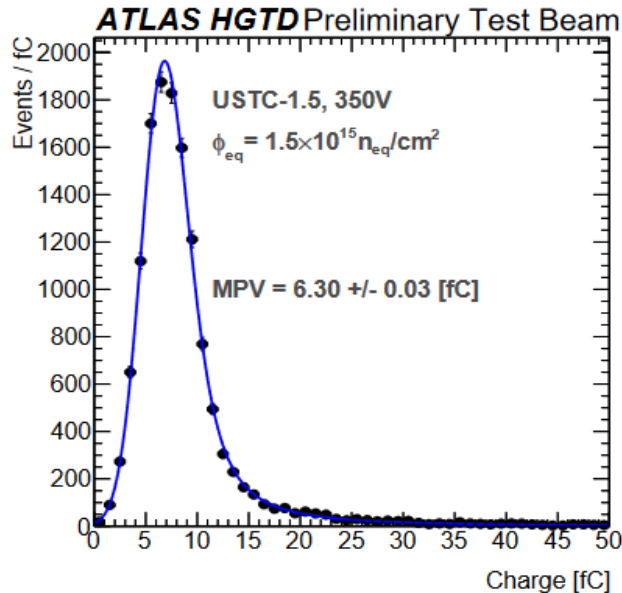
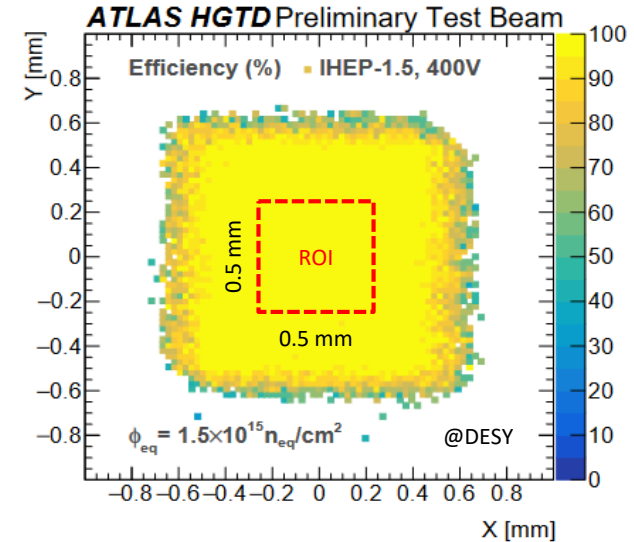
- Tested collected charge, time resolution and hit efficiency of C-enriched prototypes from 3 vendors (FBK, USTC-IME and IHEP-IME)
- LGAD (CNM-0) was used as a time reference at CERN as well as a SiPM device at DESY
- Sensors were exposed to fluences up to $1.5 \times 10^{15} n_{eq}/cm^2$ and $2.5 \times 10^{15} n_{eq}/cm^2$ at the TRIGA reactor in Ljubljana, Slovenia with fast neutrons
- Bias voltages were kept lower than the SEB voltage

Device name	Vendor	Sensor ID	Implant	Irradiation type	Fluence [n_{eq}/cm^2]	Tested at
CNM-0	CNM	W9LGA35	boron	unirradiated	—	DESY/CERN
FBK-1.5	FBK	UFSD3.2 W19	boron + carbon	neutrons	1.5×10^{15}	DESY/CERN
FBK-2.5	FBK	UFSD3.2 W19	boron + carbon	neutrons	2.5×10^{15}	DESY/CERN
USTC-1.5	USTC-IME	v2.1 W17	boron + carbon	neutrons	1.5×10^{15}	DESY
USTC-2.5	USTC-IME	v2.1 W17	boron + carbon	neutrons	2.5×10^{15}	DESY
IHEP-1.5	IHEP-IME	v2 W7 Q2	boron + carbon	neutrons	1.5×10^{15}	DESY/CERN
IHEP-2.5	IHEP-IME	v2 W7 Q2	boron + carbon	neutrons	2.5×10^{15}	CERN

Device name	V_{g10} [V]	Diffusion	c [cm^2]
FBK-1.5/2.5	50	H	1.73×10^{-16}
USTC-1.5/2.5	27	L	1.23×10^{-16}
IHEP-1.5/2.5	25	CHBL	1.14×10^{-16}

Collected charge

- Distribution of charge in the Region of Interest (ROI) was fitted with a Landau-Gaussian convoluted function
- Collected charge:
 - Defined as the Most Probable Value (MPV) from fit
 - Above the minimum required charge of 4 fC needed for a good timing measurement with the HGTD project

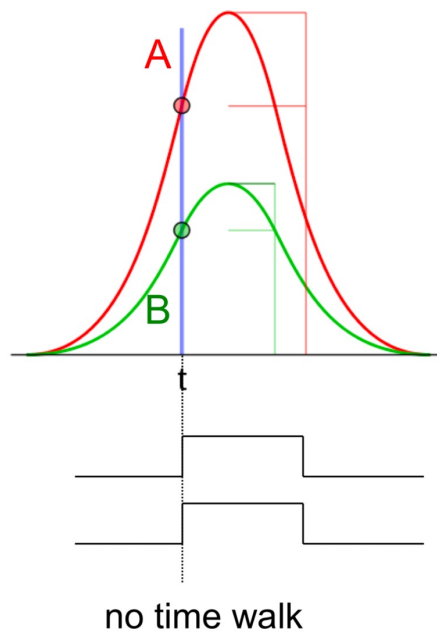
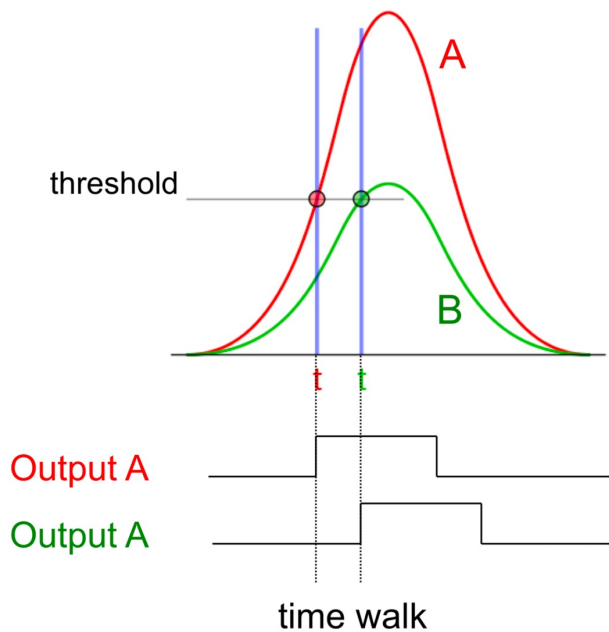


Time resolution method

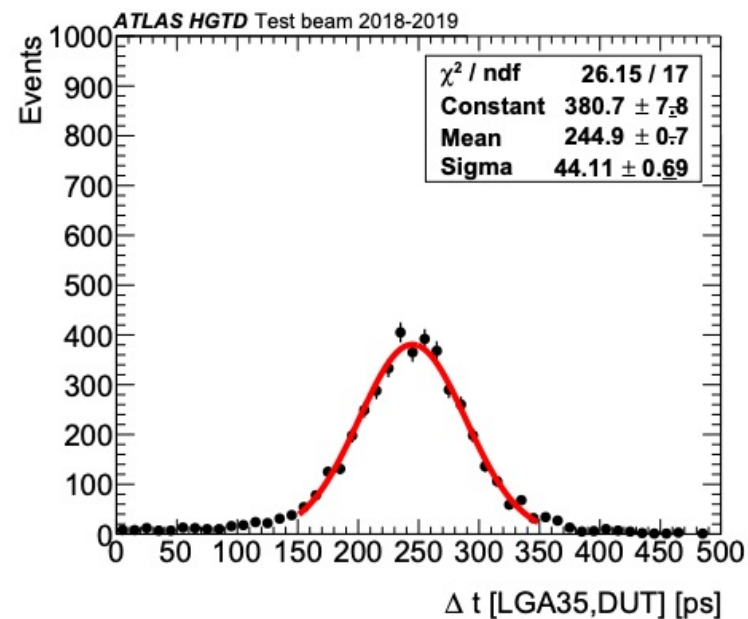
- Constant Fraction Discrimination (CFD) method was used to calculate Time of Arrival (TOA) to minimize the contribution of time walk: 20% for the SiPM and 50% for the irradiated LGADs
- To extract the LGADs' time resolution, the distribution of the difference between the TOA (ΔTOA) of the LGADs and that of the time reference device were fitted with a Gaussian function, each of them giving a width σ_{ij}

Constant Threshold Discriminator (CTD)

Constant Fraction Discrimination (CFD)

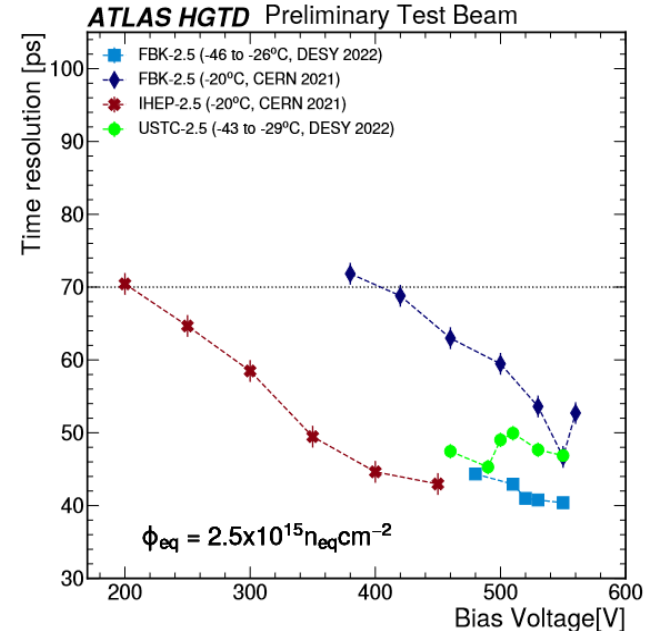
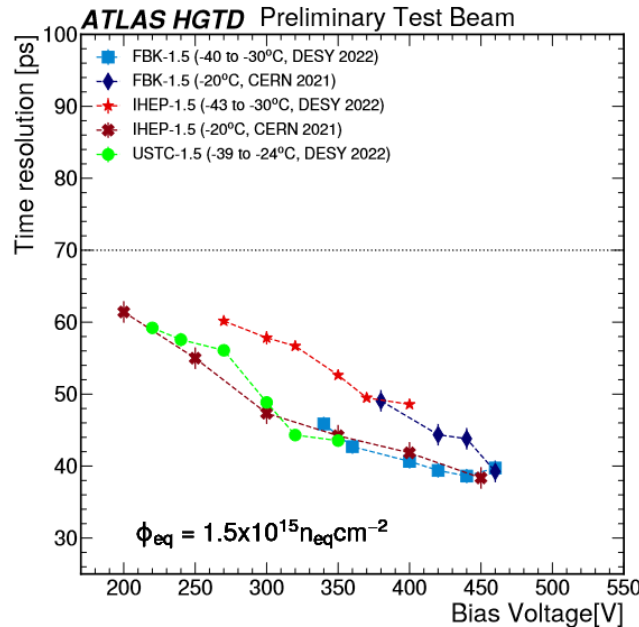
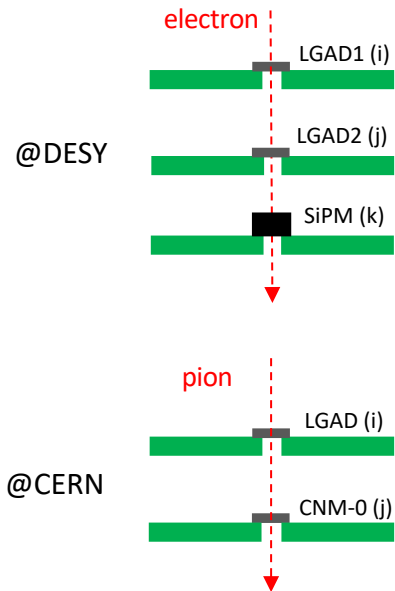


[C. Agapopoulou et al., 2022 JINST 17 P09026](#)



Time resolution

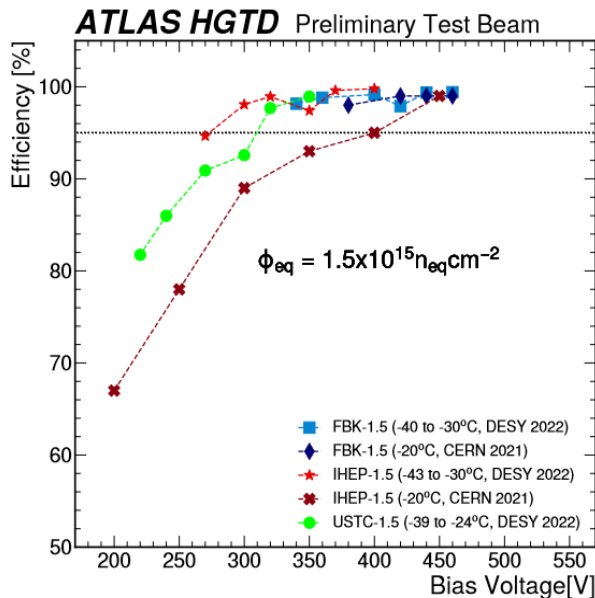
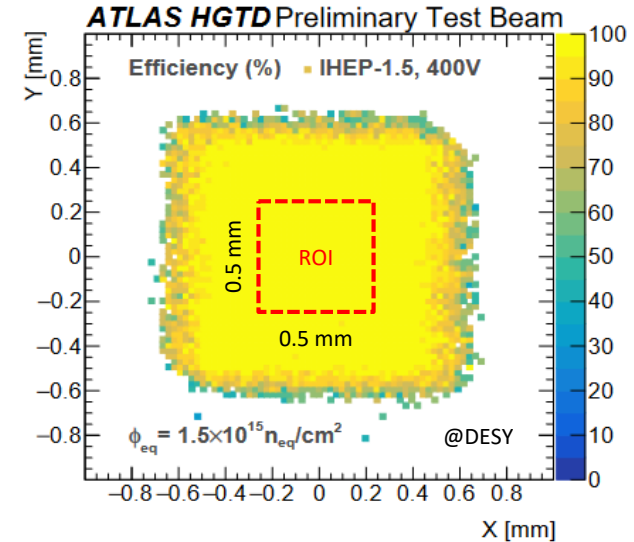
- For set-up at DESY, the ΔTOA of three devices is σ_{ij} , σ_{ik} and σ_{jk} , respectively. So the time resolution of LGADs and reference SiPM are $\sigma_i = \sqrt{(\sigma_{ij}^2 + \sigma_{ik}^2 - \sigma_{jk}^2)/2}$, $\sigma_j = \sqrt{(\sigma_{ij}^2 + \sigma_{jk}^2 - \sigma_{ik}^2)/2}$ and $\sigma_k = \sqrt{(\sigma_{ik}^2 + \sigma_{jk}^2 - \sigma_{ij}^2)/2}$ ($\sigma_{\text{SiPM}(k)} = 62.6$ ps)
- For set-up at CERN, $\sigma_i = \sqrt{\sigma_{ij}^2 - \sigma_j^2}$ (the reference CNM-0 is known, which means $\sigma_j = 55$ ps)



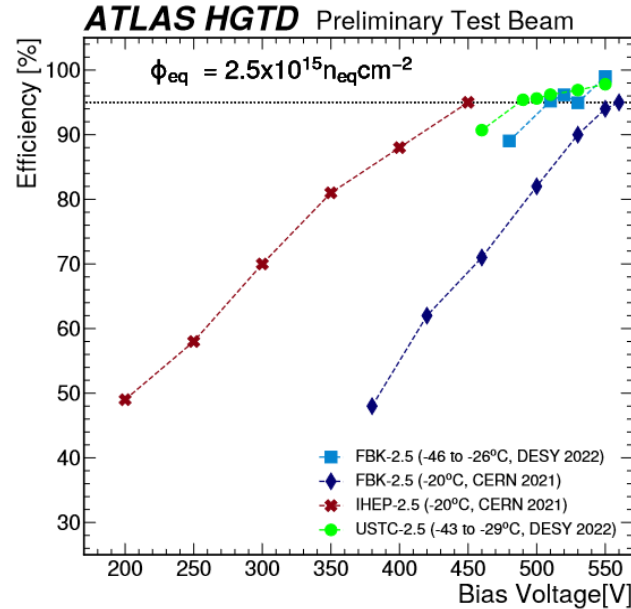
Hit efficiency

$$\text{Hit Efficiency} = \frac{\text{Resconstructed tracks with } q > Q_{\text{cut}}}{\text{Total resconstructed tracks}}$$

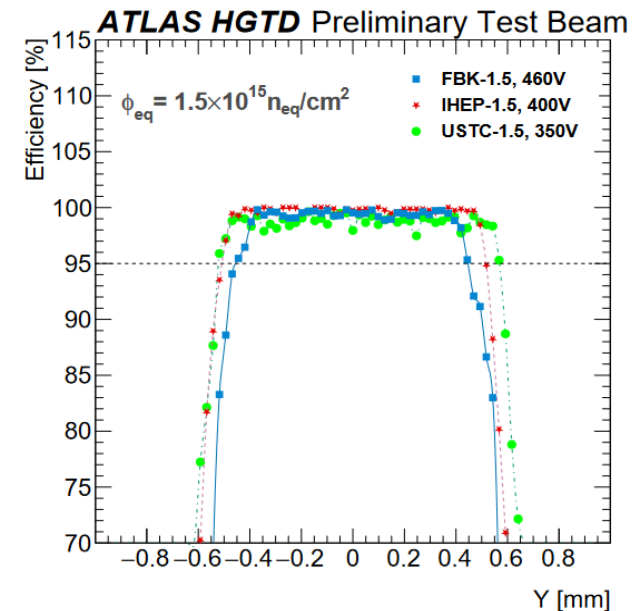
- Q_{cut} is set to 2 fC, the minimum achievable threshold of the ALTIROC chip
- Achieved the efficiency of 95% required for HGTD after irradiation



Kuo Ma



PSD13, Oxford, 2023



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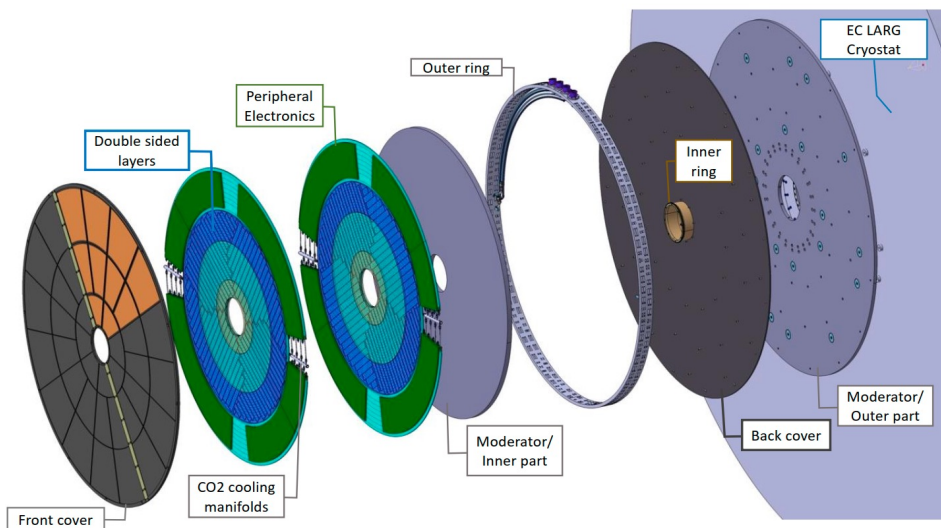
Summary and outlook

- The LGAD, as a **fast timing as well as radiation hard** silicon based detector, has reached a mature state in recent years
- **Carbon-enriched LGADs** from three vendors (**FBK, IHEP-IME and USTC-IME**) have been studied both in terms of radiation hardness and performance
 - irradiated at fluences of $1.5 - 2.5 \times 10^{15} \text{ n}_{\text{eq}}/\text{cm}^2$, the LGADs were operated at voltages below 550 V
 - Under these conditions, LGADs achieved the objectives of:
 - Collected charge of more than **4 fC** while guaranteeing an optimal time resolution better than **70 ps**
 - An efficiency larger than **95%** uniformly over sensors' surface is obtained with a charge threshold of 2 fC
- These results confirm the feasibility of an LGAD-based timing detector for HL-LHC
- Outlook:
 - The **IHEP-IME and USTC-IME** Pre-production have been started and the laboratory test is ongoing, looking forward to do beam test soon

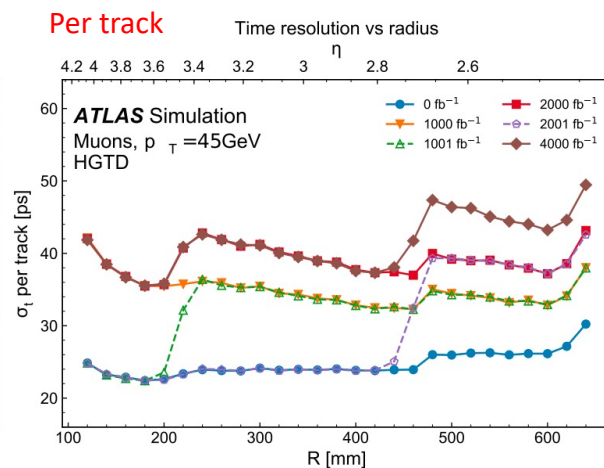
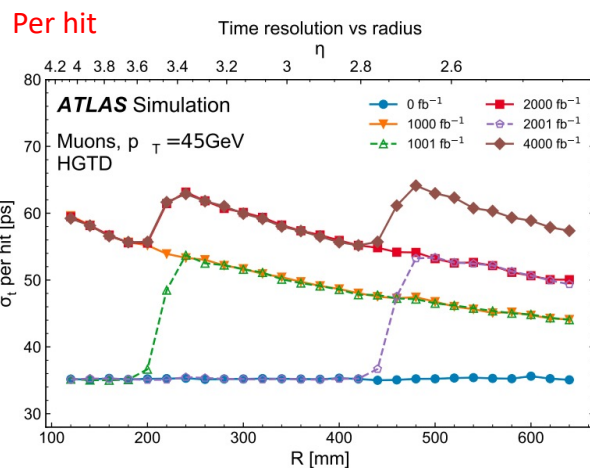
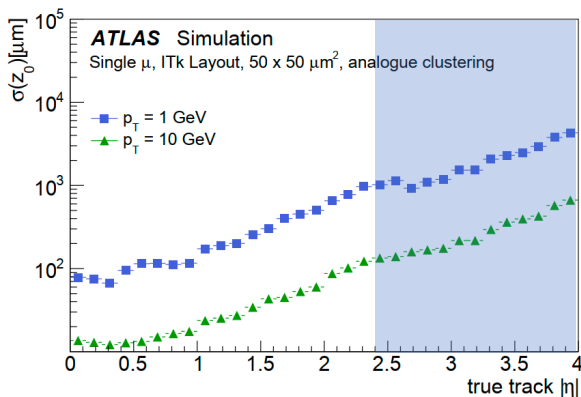
Thanks for your attention!

Back up

HGTD: Layout and requirements

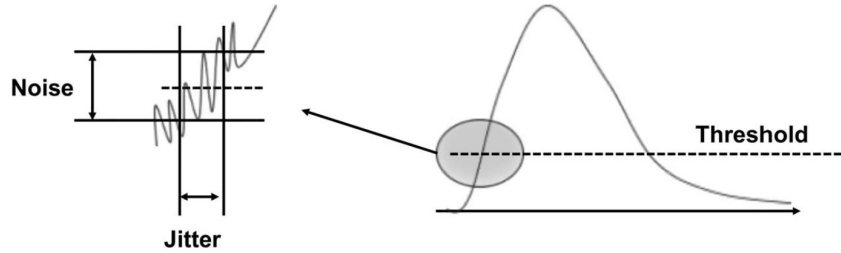


Pseudo-rapidity coverage	$2.4 < \eta < 4.0$
Thickness in z	75 mm (+50 mm moderator)
Position of active layers in z	± 3.5 m
Weight per end-cap	350 kg
Radial extension:	
Total	$110 \text{ mm} < r < 1000 \text{ mm}$
Active area	$120 \text{ mm} < r < 640 \text{ mm}$
Pad size	$1.3 \text{ mm} \times 1.3 \text{ mm}$
Active sensor thickness	50 μm
Number of channels	3.6 M
Active area	6.4 m ²
Module size	30 x 15 pads (4 cm x 2 cm)
Modules	8032
Collected charge per hit	$> 4.0 \text{ fC}$
Average number of hits per track	
$2.4 < \eta < 2.7$ ($640 \text{ mm} > r > 470 \text{ mm}$)	≈ 2.0
$2.7 < \eta < 3.5$ ($470 \text{ mm} > r > 230 \text{ mm}$)	≈ 2.4
$3.5 < \eta < 4.0$ ($230 \text{ mm} > r > 120 \text{ mm}$)	≈ 2.6
Average time resolution per hit (start and end of operational lifetime)	
$2.4 < \eta < 4.0$	$\approx 35 \text{ ps}$ (start), $\approx 70 \text{ ps}$ (end)
Average time resolution per track (start and end of operational lifetime)	$\approx 30 \text{ ps}$ (start), $\approx 50 \text{ ps}$ (end)



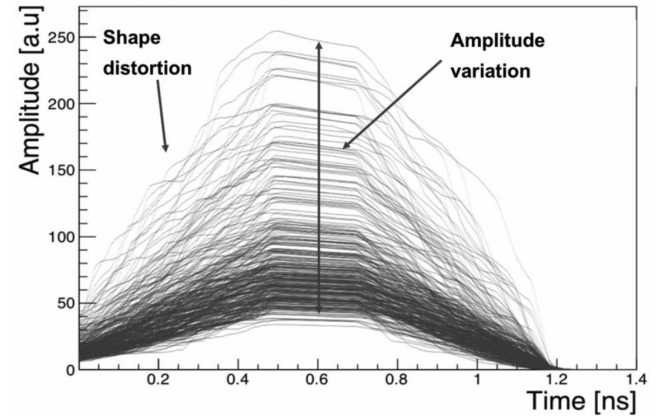
Introduction to the contribution of time resolution

- Jitter



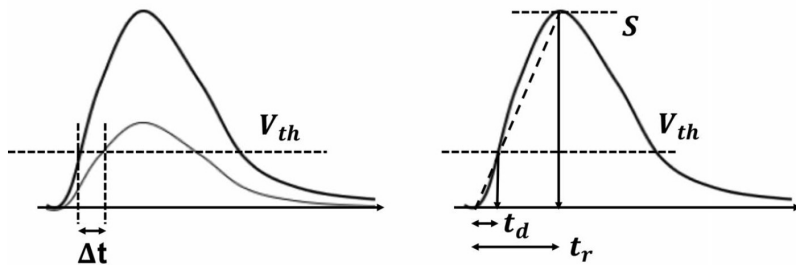
$$\sigma_{\text{Jitter}} = \frac{N}{dV/dt} \approx \frac{t_{\text{rise}}}{S/n}$$

- Landau noise



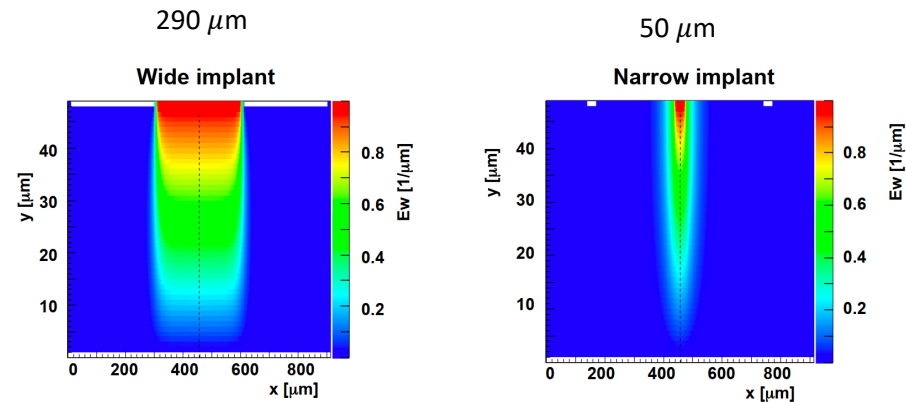
WF2 simulation, MIP, 50 μm , Gain ~ 20

- Time walk



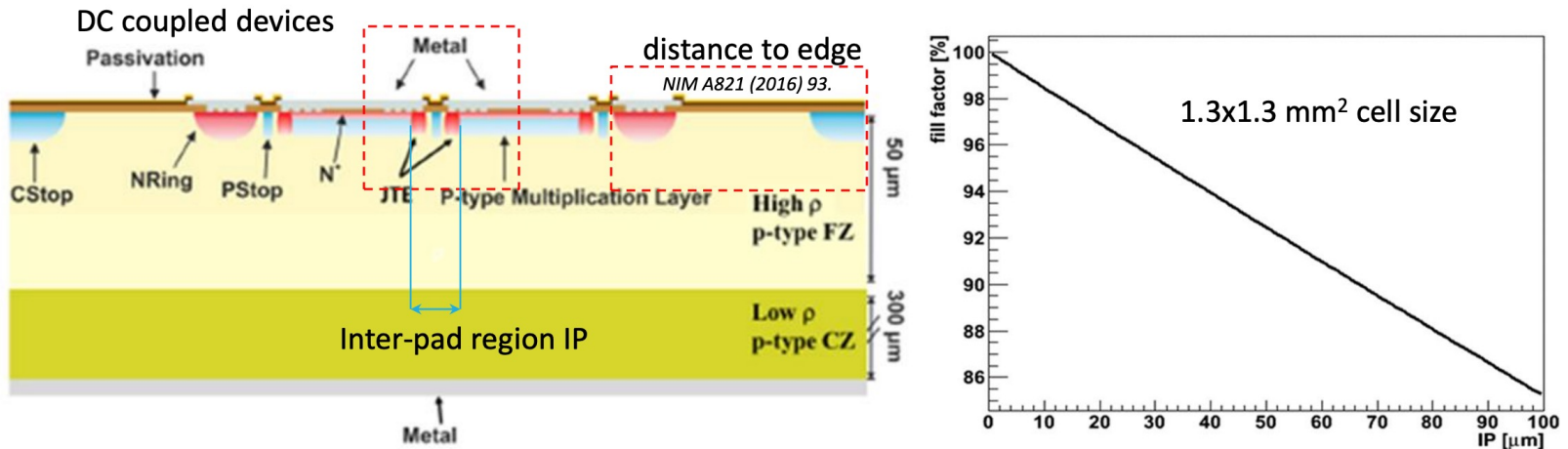
$$\sigma_{\text{TimeWalk}} = [t_d]_{\text{RMS}} = \left[\frac{V_{th}}{S/t_{\text{rise}}} \right]_{\text{RMS}} \propto \left[\frac{N}{dV/dt} \right]_{\text{RMS}}$$

- Distortion (distribution of weighting field)



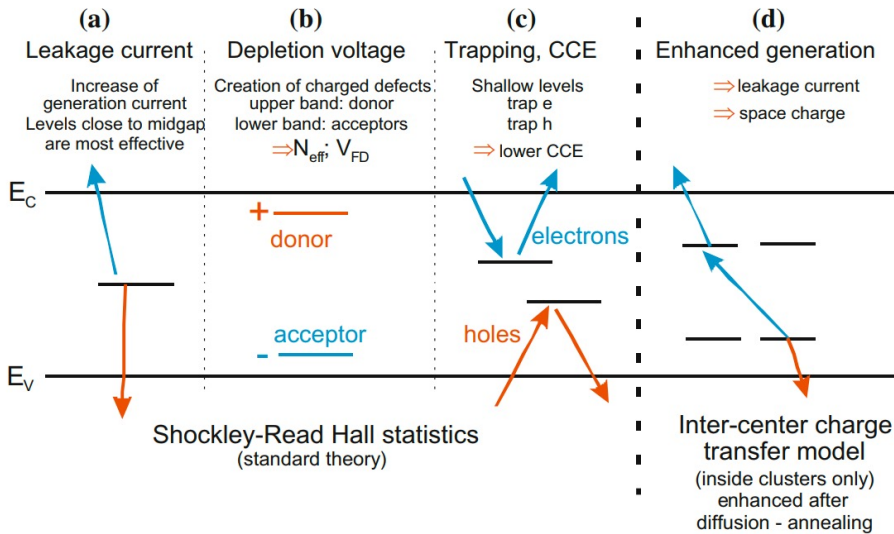
Segmented LGADs and Inter-pad region

[Gregor, Detector Seminar, 2021](#)



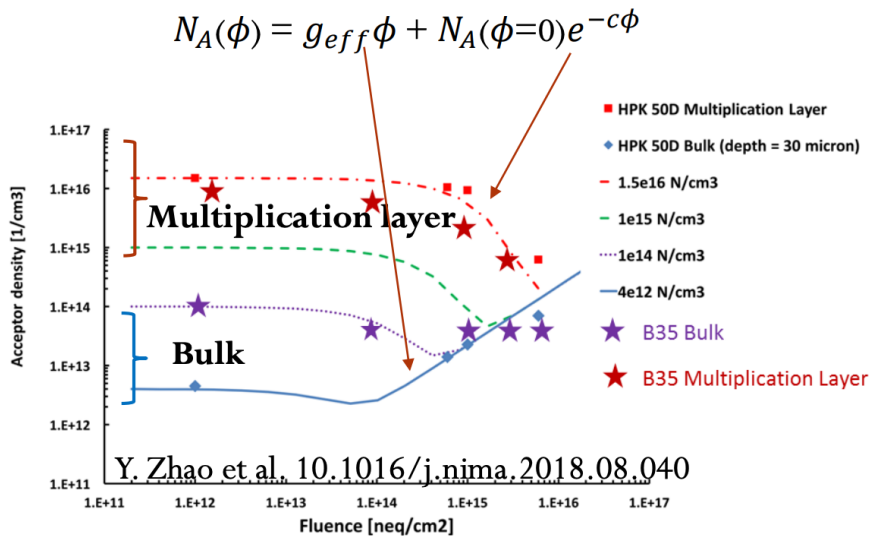
- JTE enables efficient isolation of the electrode – allows for segmentation of the LGAD – the key to multi electrode LGADs
- Inter-pad region is the distance between two electrodes. It is effectively the non-active region as it is without the gain and effectively reduces the “fill factor” of the LGAD
- The IP distance can't be too small as in a case of a bad connection – floating pad there is a danger of an early breakdown (~30-90 μm)
- Distance to edge determines the breakdown through the edges and is 300-500 μm

Radiation effect on Silicon



Three main effect:

- Increase of leakage current
- Changes in doping concentration
- Decrease of charge collection



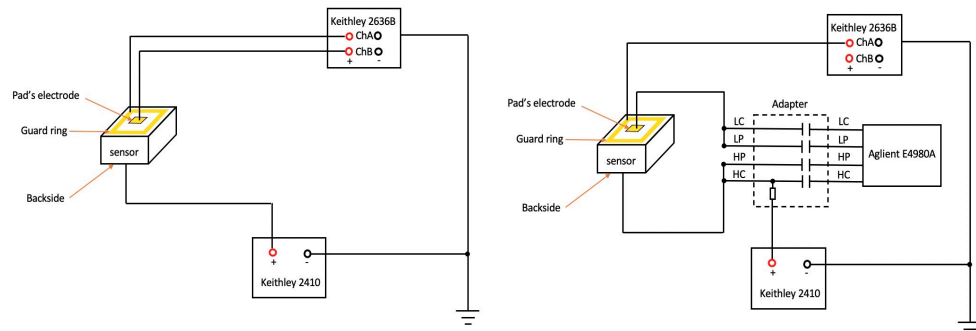
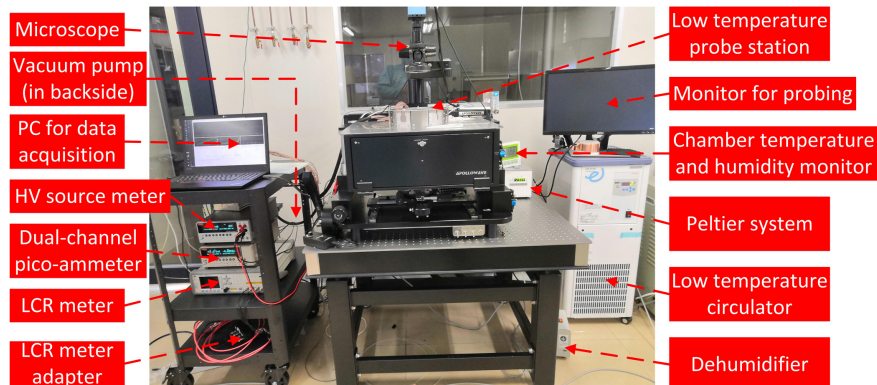
- Acceptor creation: $g_{eff}\phi$
 - By creation of deep traps
- Acceptor removal mechanism: $N_A(\phi = 0)e^{-c\phi}$
 - Reduction of doping \rightarrow reduction of gain
 - **C-factor (acceptor removal constant)** depending on detector type (the lower the better)

[S. M. Mazza et al, PSD12, 2021](#)

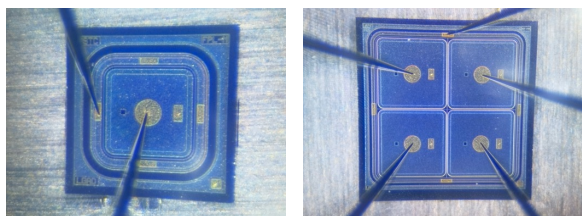
Experimental techniques for LGADs

Experimental Techniques	Purposes	Comments
Leakage current-Voltage (IV)	Gain layer depletion voltage (V_{GL}^I)	Doping information of gain layer
	Device break down voltage (V_{BD})	Safe operating voltage range
	Leakage current@ V_x or voltage@ I_x	Power consumption of circuit
	Inter pad resistance	Isolation between pads
Capacitance-Voltage (CV)	Gain layer depletion voltage (V_{GL}^C)	Depletion behavior of gain layer
	Full depletion voltage of the device (V_{FD})	Depletion behavior of bulk
	Electrode capacitance (C_{pad})	Depletion behavior of sensor
	Inter pad capacitance	Cross talk between pads
Beta-scope test (^{90}Sr)	Voltage required to collect 15 fC (V_{15fC})	Voltage required to collect 15 fC at -30°C
	Minimum operation voltage ($V_{op,min}$)	S/N>10, V>4fC, noise < 1.2 noise at low bias, no ghosts, I<500nA/5 μ A
	Maximum operation voltage ($V_{op,max}$)	The above conditions can be met
	Time resolution at 4fC (τ_{4fC})	Time resolution at $V_{op,min}$
Transient Current Technology (TCT, laser)	The no-gain distance between two adjacent pads (Effective IP width)	No-gain area where collected charge is less than 50%*Max (collected charge)
Test Beam (TB, proton or electron or ...)	Hit efficiency	97% (95%) at the start (end)
	Charge collection and timing resolution	35 ps (start), 70 ps (end) per hit

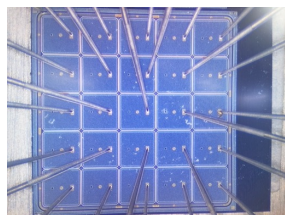
IV & CV setup (USTC for example)



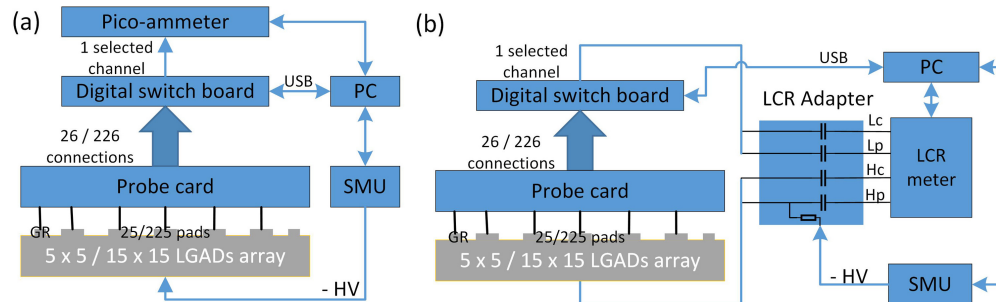
Equivalent circuit diagram of 1×1 LGADs



Tested by probe needles



Tested by probe card



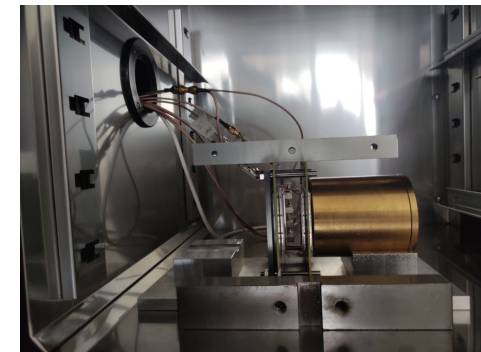
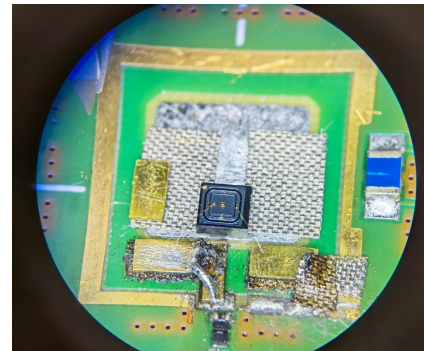
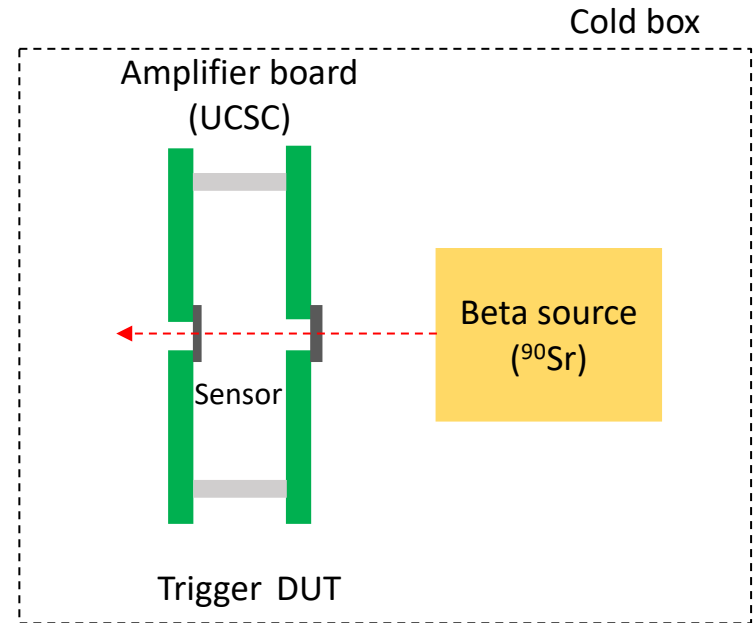
Equivalent circuit diagram of 15×15 LGADs

[J.J. Ge, NIMA, 2021](#)

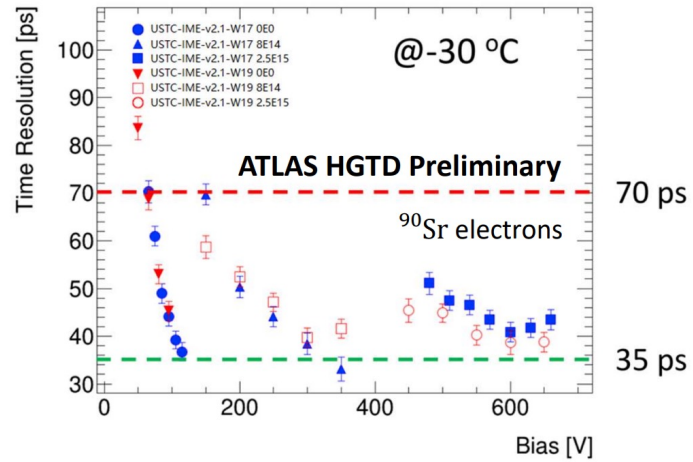
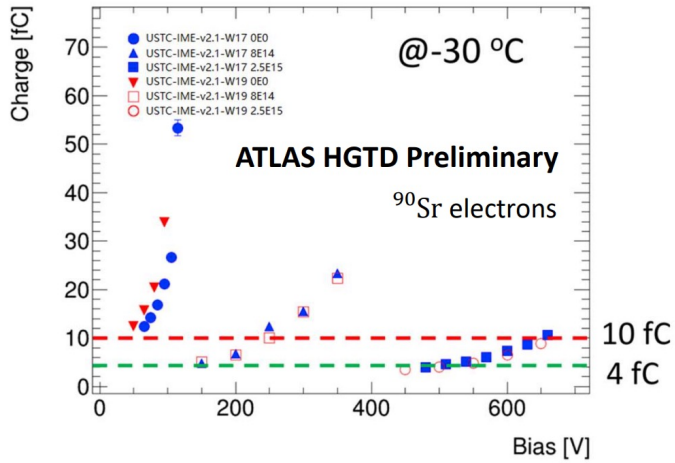
β -scope setup (USTC for example)

[C.H. Li, NIMA, 2022](#)

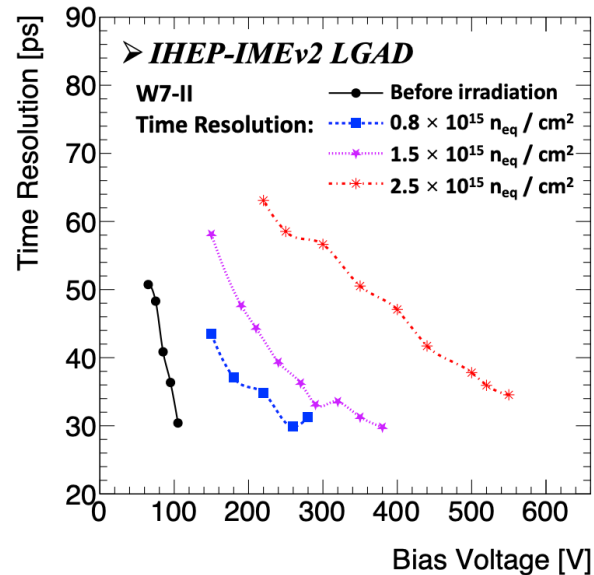
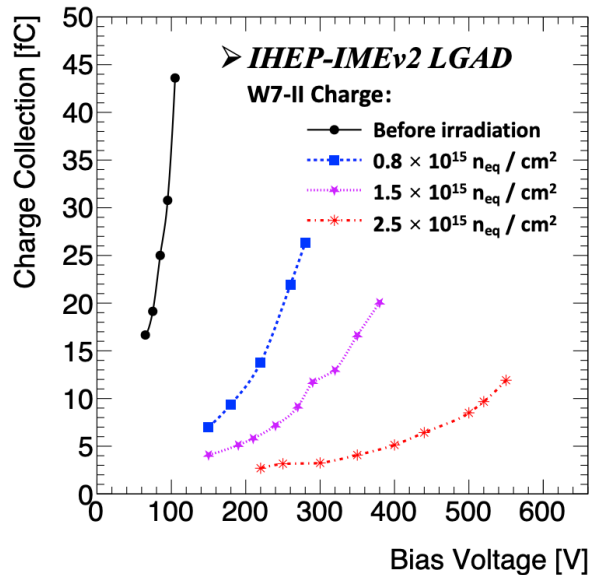
- Temperature: -30 °C
- Trigger
 - Sensor (HPK Type1.1, un-irradiated) & Pre-amplifier board
 - With the 2nd stage amplifier
 - Bias: -165.00 V
 - σ_t : 33.88 ps
- DUT (Device Under Test)
 - Sensor & Pre-amplifier board
 - With the 2nd stage amplifier
- Oscilloscope
 - Sampling rate: 20 Gs/s
 - Bandwidth: 1 GHz



Performance of IME-LGAD prototypes with ^{90}Sr



[ATLAS HGTD Public Plots](#)

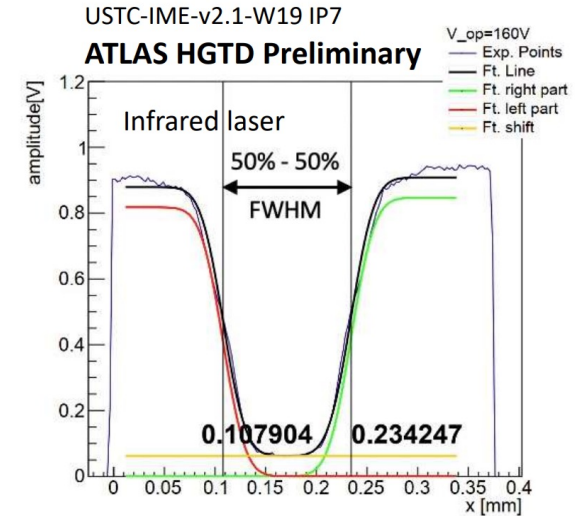
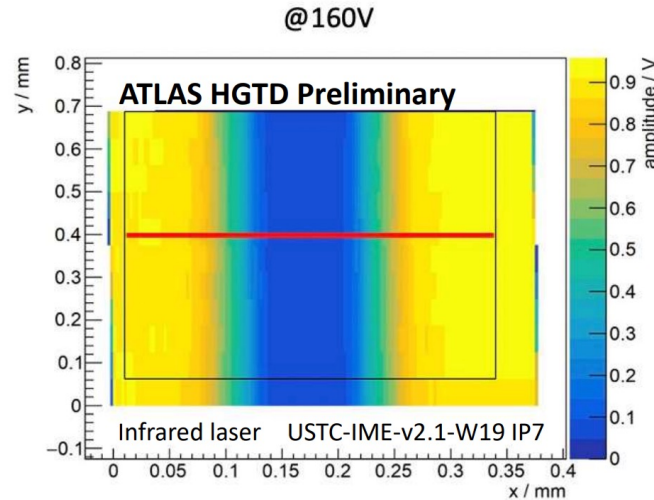
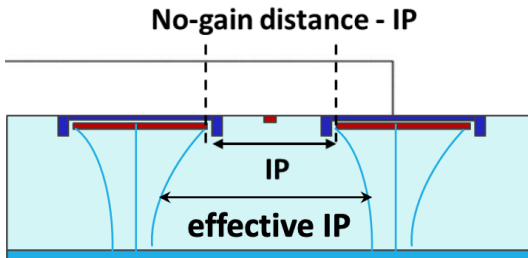


[K. Wu et al NIMA, 2022](#)

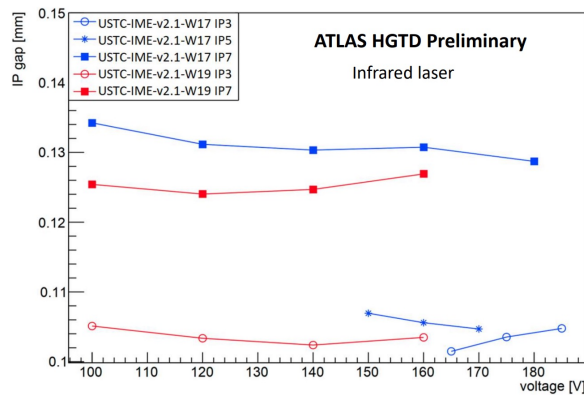
Inter-pad (IP) gap measurements

Laser (infra-red, 1064 nm)

[ATLAS HGTD Public Plots](#)



IP variation with voltage

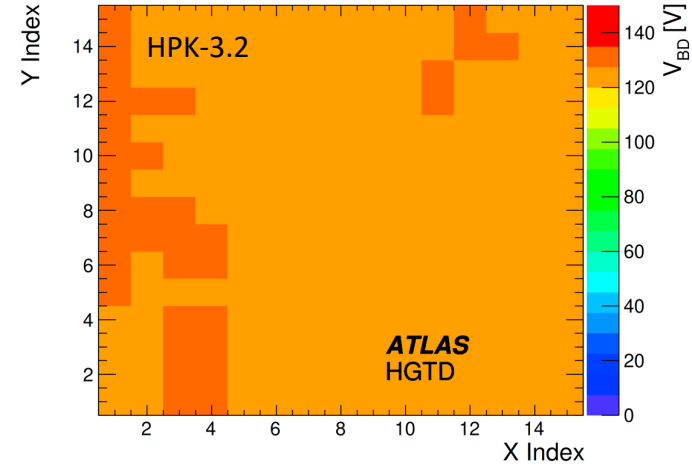
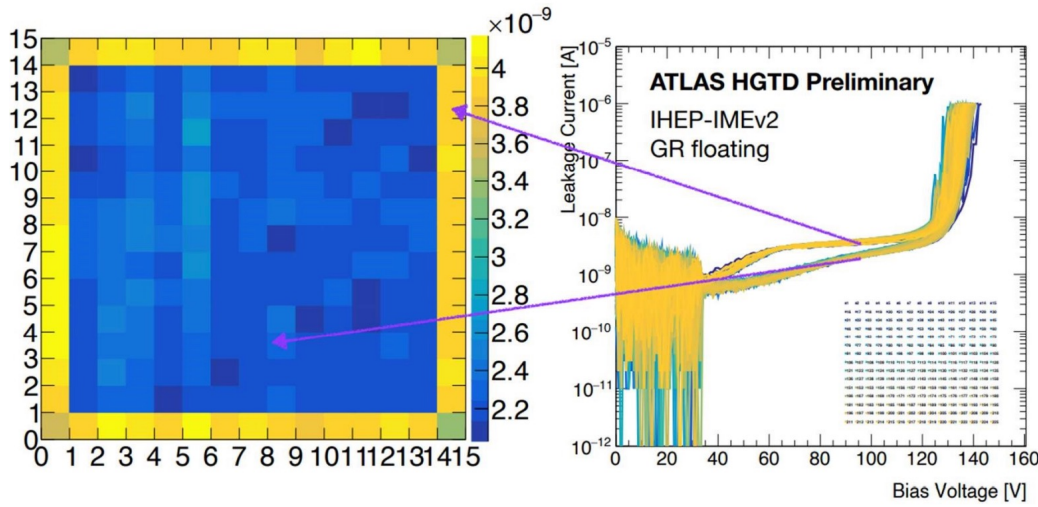


Wafer	IP _{nominal} (Nominal IP)	IP _{eff} (Effective IP)	IP _{eff} - IP _{nominal}
W17	30um	100um	70um
	50um	107um	57um
	70um	130um	60um
W19	30um	103um	73um
	70um	124um	54um

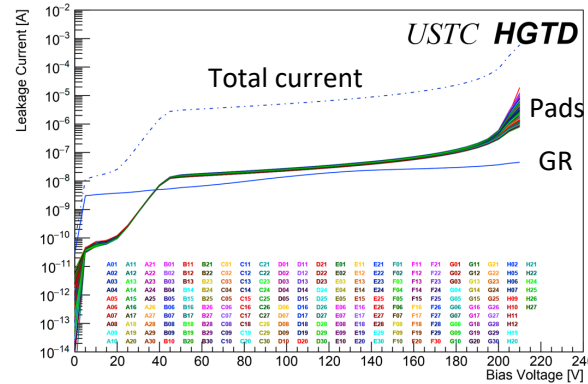
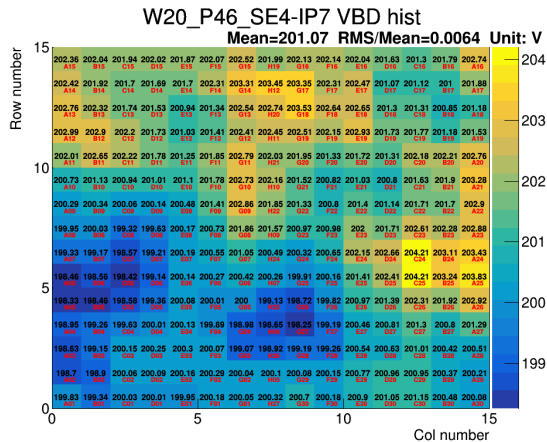
- For IP3 and IP5, the effective IP gap is about 100 um. For IP7, the effective IP gap is about 130 um.
- Effective IP gap is large than nominal IP gap from 50-75 um.

Uniformity of full-size (15×15) LGADs

- Tested by single probe needle (neighbors and GR floating)



- Tested by probe card (neighbors and GR are grounded)



- Very homogenous breakdown voltage (V_{BD} , $I_{pad} < 500$ nA)
- GR floating affects the outermost pads for IHEP-IME v2 LGADs